Surface Mount Power Resistor
Thick Film Technology

FEATURES

- **AEC-Q200 qualified**
- 35 W at 25 °C case temperature
- Surface mounted resistor - TO-263 (D^2PAK) style package
- Wide resistance range from 1 Ω to 14 kΩ
- Non inductive
- Higher pulse absorption, up to 15 J/0.1 s
- Solder reflow secure at 270 °C/10 s
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE

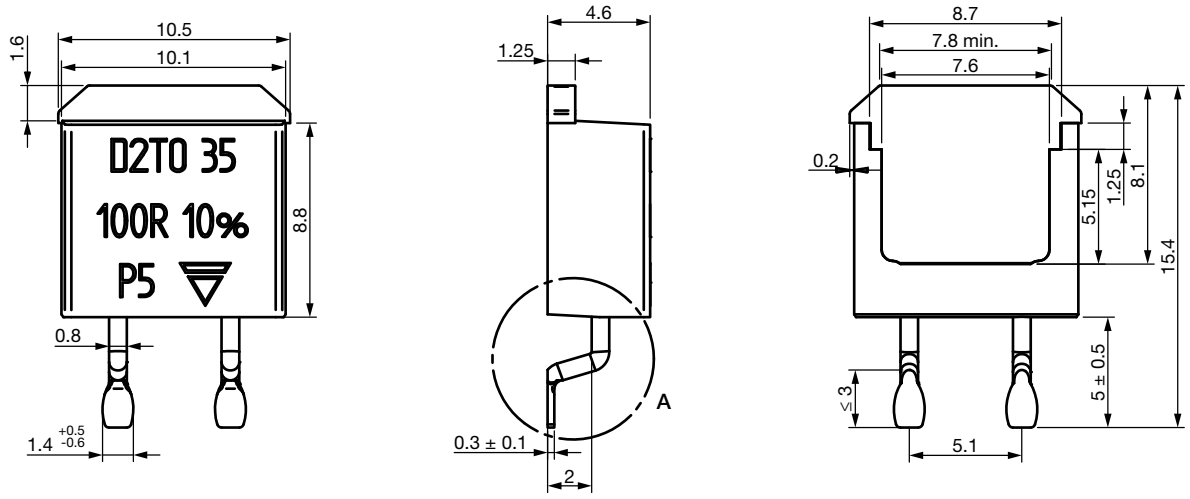
RoHS COMPLIANT

LINKS TO ADDITIONAL RESOURCES

3D Models

D2TO35 H is the extension of D2TO35. This unique design is able to absorb 30 % more energy than standard D2TO35.

DIMENSIONS in millimeters



Notes

- For the assembly on board, we recommend the lead (Pb)-free thermal profile as per J-STD-020C
- Power dissipation is 3.5 W at an ambient temperature of 25 °C when mounted on a double sided copper board using FR4 HTG, 70 µm of copper, 39 mm x 30 mm x 1.6 mm, with thermal vias
- Planarity measurement according to JEDEC® TO-263D

STANDARD ELECTRICAL SPECIFICATIONS

MODEL	SIZE	RESISTANCE RANGE Ω	RATED POWER $P_{25\,°C}$ W	LIMITING ELEMENT VOLTAGE U_L V	TOLERANCE ± %	TEMPERATURE COEFFICIENT ± ppm/°C	CRITICAL RESISTANCE Ω
D2TO35H	TO-263	1 to 14K	35	500	2, 5, 10	150	7.14K

MECHANICAL SPECIFICATIONS

Mechanical Protection	Molded
Resistive Element	Thick film
Substrate	Alumina
Connections	Tinned copper
Weight	3 g max.

ENVIRONMENTAL SPECIFICATIONS

Temperature Range	-55 °C to +175 °C
Flammability	IEC 60695-11-5 Application time: t_a = 10 s Burning duration: t_b < 30 s

TECHNICAL SPECIFICATIONS	
Power Rating and Thermal Resistance of the Component	35 W at 25 °C (case temperature) $R_{TH\ (j\ -\ c)}$: 4.28 °C/W
Temperature Coefficient	See Special Features table
Standard	± 150 ppm/°C
Dielectric Strength IEC 60115-1	2000 V_{RMS} - 1 min - 10 mA max. (between terminals and board)
Insulation Resistance	≥ 10^4 MΩ
Inductance	≤ 0.1 µH

DIMENSIONS	
Standard Package	TO-263 style (D^2PAK)

SPECIAL FEATURES	
Resistance Values	≥ 1
Tolerances	± 2 % at ± 10 %
Requirement Temperature Coefficient (TCR) (-55 °C +150 °C) IEC 60115-1	± 150 ppm/°C

PERFORMANCE

TESTS	CONDITIONS	REQUIREMENTS
Momentary Overload	IEC 60115-1 §4.13 1.7 Pr 5 s for $R < 2\ \Omega$ 1.4 Pr 5 s for $R \geq 2\ \Omega$ US < 1.5 UL	± (0.25 % + 0.005 Ω)
Load Life	IEC 60115-1 1000 h, 90/30 Pr at +25 °C	± (0.5 % + 0.005 Ω)
High Temperature Exposure	AEC-Q200 rev. D conditions: MIL-STD-202 method 108 1000 h, +175 °C, unpowered	± (0.25 % + 0.005 Ω)
Temperature Cycling	Pre-conditioning 3 reflows according JESTD020D IEC 60068-2-14 test Na 1000 cycles, -55 °C, +175 °C Dwell time - 15 min	± (0.5 % + 0.005 Ω)
Moisture Resistance	AEC-Q200 rev. D conditions: MIL-STD-202 method 106 10 cycles, 24 h, unpowered	± (0.5 % + 0.005 Ω)
Biased Humidity	AEC-Q200 rev. D conditions: MIL-STD-202 method 103 1000 h, 85 °C, 85% RH	± (0.5 % + 0.005 Ω)
Operational Life	AEC-Q200 rev. D conditions: Pre-conditioning 3 reflows according JESTD020D MIL-STD-202 method 108 2000 h, 90/30, powered, +125 °C	± (0.5 % + 0.005 Ω)
ESD Human Body Model	AEC-Q200 rev. D conditions: AEC-Q200-002 25 kV_{AD}	± (0.5 % + 0.005 Ω)
Vibration	AEC-Q200 rev. D conditions: MIL-STD-202 method 204 5 *g*'s for 20 min, 12 cycles test from 10 Hz to 2000 Hz	± (0.2 % + 0.005 Ω)
Mechanical Shock	AEC-Q200 rev. D conditions: MIL-STD-202 method 213 100 *g*'s, 6 ms, 3.75 m/s 3 shocks/direction	± (0.2 % + 0.005 Ω)
Board Flex	AEC-Q200 rev. D conditions: AEC-Q200-005 bending 2 mm, 60 s	± (0.25 % + 0.01 Ω)
Terminal Strength	AEC-Q200 rev. D conditions: AEC-Q200-006 1.8 kgf, 60 s	± (0.25 % + 0.01 Ω)

ASSEMBLY SPECIFICATIONS		
For the assembly on board, we recommend the lead (Pb)-free thermal profile as per J-STD-020C		
TESTS	**CONDITIONS**	**REQUIREMENTS**
Resistance to Soldering Heat	IEC 60115-1 IEC 60068-2-58 Solder bath method: 270 °C/10 s	± (0.5 % + 0.005 Ω)
Moisture Sensitivity Level (MSL)	IPC/JEDEC® J-STD-020C 85 °C / 85 % RH / 168 h	Level: 1 + pass requirements of TCR overload and dielectric strength after MSL

CHOICE OF THE BOARD

The user must choose the board according to the working conditions of the component (power, room temperature). Maximum working temperature must not exceed 175 °C. The dissipated power is simply calculated by the following ratio:

$$P = \frac{\Delta T}{R_{TH\ (j\ -\ c)} + R_{TH\ (c\ -\ h)} + R_{TH\ (h\ -\ a)}} \quad (1)$$

P: expressed in W

ΔT: difference between maximum working temperature and room temperature or fluid cooling temperature

$R_{TH\ (j\ -\ c)}$: thermal resistance value measured between resistive layer and outer side of the resistor. It is the thermal resistance of the component: 4.28 °C/W.

$R_{TH\ (c\ -\ h)}$: thermal resistance value measured between outer side of the resistor and upper side of the board. This is the thermal resistance of the solder layer.

$R_{TH\ (h\ -\ a)}$: thermal resistance of the board.

Example:

$R_{TH\ (c\ -\ h)} + R_{TH\ (h\ -\ a)}$ for D2TO35 power rating 3.5 W at ambient temperature +25 °C.
Thermal resistance $R_{TH\ (j\ -\ c)}$: 4.28 °C/W
Considering equation (1) we have:

$\Delta T = 175\ °C - 25\ °C = 150\ °C$

$R_{TH\ (j\ -\ c)} + R_{TH\ (c\ -\ h)} + R_{TH\ (h\ -\ a)} = \Delta T/P = 150/3.5 = 42.8\ °C/W$

$R_{TH\ (c\ -\ h)} + R_{TH\ (h\ -\ a)} = 42.8\ °C/W - 4.28\ °C/W = 38.52\ °C/W$

Single Pulse:

These informations are for a single pulse on a cold resistor at 25 °C (not already used for a dissipation) and for pulses of 100 ms maximum duration.

The formula used to calculate *E* is:

$$E = P \times t = \frac{U^2}{R} \times t$$

with:

E (J): pulse energy

P (W): pulse power

t (s): pulse duration

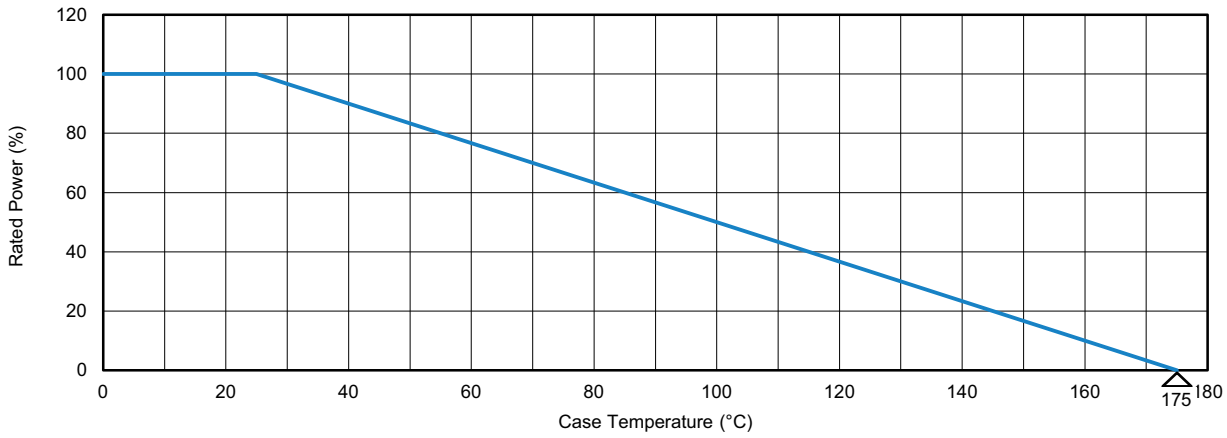
U (V): pulse voltage

R (Ω): resistor

The energy calculated must be less: than that allowed by the graph.

POWER RATING

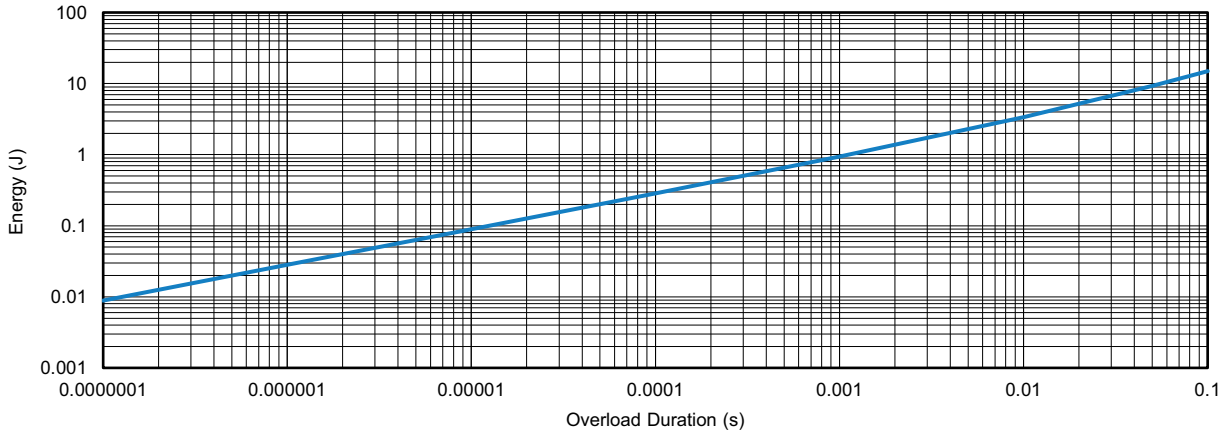
The temperature of the case should be maintained within the limits specified.



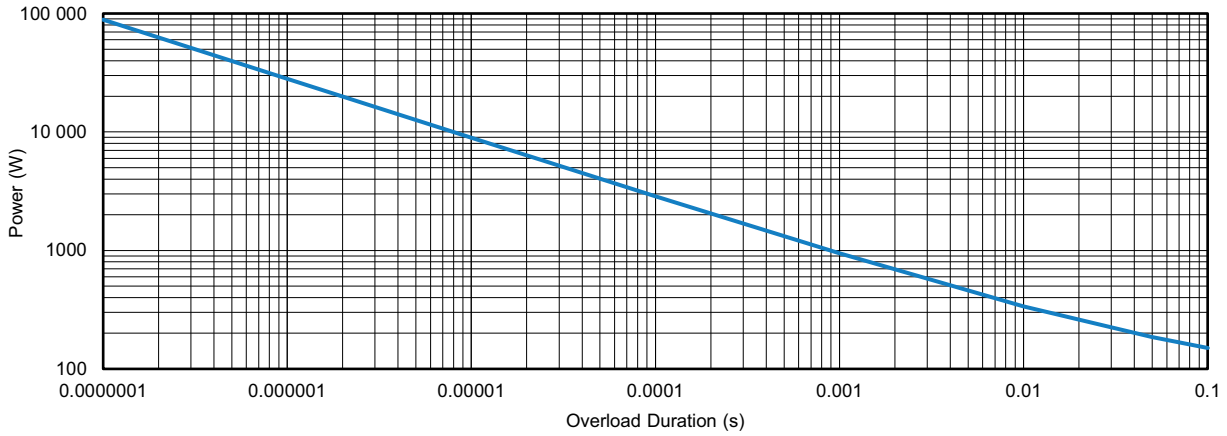
OVERLOADS

In any case the applied voltage must be lower than the maximum overload voltage of 750 V. The values indicated on the graph below are applicable to resistors in air or mounted onto a board.

ENERGY CURVE

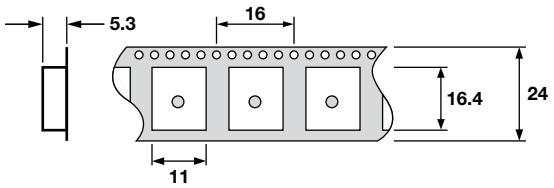


POWER CURVE



PACKAGING

- Reel
- Tube
- Tape dimensions (mm) for reel:



MARKING

Model, style, resistance value (in Ω), tolerance (in %), manufacturing date, Vishay Sfernice trademark

ORDERING INFORMATION

D2TO	35	H	14 kΩ	± 5 %	XXX	e3
MODEL	STYLE	HIGH PULSE	RESISTANCE VALUE	TOLERANCE	CUSTOM DESIGN	LEAD (Pb)-FREE
				G = ± 2 % J = ± 5 % K = ± 10 %	Optional on request: shape, etc.	

SAP PART NUMBERING GUIDELINES

D	2	T	O	0	3	5	H	R	2	0	0	0	K	R	E	3

GLOBAL MODEL	SIZE	INFO PULSE	OHMIC VALUE	TOLERANCE	PACKAGING	LEAD (Pb)-FREE
D2TO	**035**	**H** = high pulse absorption	The first four digits are significant figures and the last digit specifies the number of zeros to follow. R designates decimal point. **48R70** = 48.7 Ω **27000** = 2700 Ω = 2.7 kΩ	**G** = 2 % **J** = 5 % **K** = 10 %	**R** = reel 500 pieces **T** = tube 50 pieces	**E3** = pure tin